# SiC Power Module

#### BSM300D12P2E001

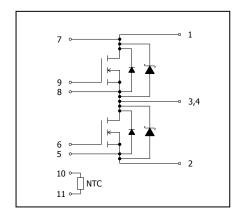
#### Application

- · Motor drive
- · Inverter, Converter
- · Photovoltaics, wind power generation.
- · Induction heating equipment.

#### Features

- 1) Low surge, low switching loss.
- 2) High-speed switching possible.
- 3) Reduced temperature dependence.

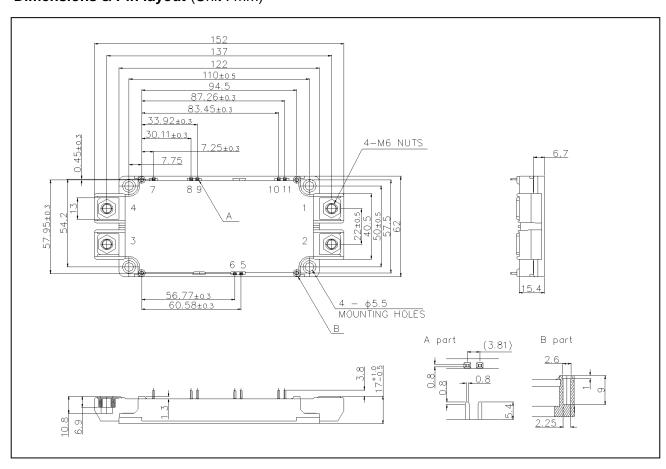
#### ●Circuit diagram



#### Construction

This product is a half bridge module consisting of SiC-DMOSFET and SiC-SBD from ROHM.

## ●Dimensions & Pin layout (Unit : mm)

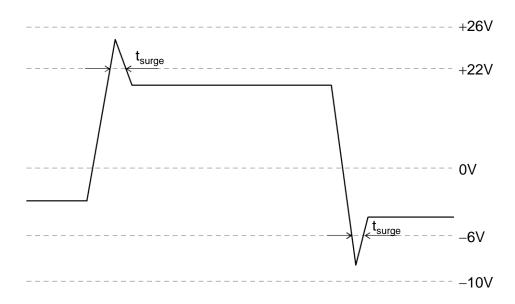


## ● Absolute maximum ratings (T<sub>i</sub> = 25°C)

Parameter	Symbol	Conditions	Limit	Unit	
Drain-source voltage	$V_{DSS}$	G-S short	1200		
Gate-source voltage(+)	$V_{GSS}$	D-S short	22	V	
Gate-source voltage(-)	V GSS	D-3 SHOIL	-6	ľ	
G - S Voltage (t <sub>surge</sub> <300nsec)	$V_{GSS\_surge}$	D-S short	-10 to 26		
Drain current *1	I <sub>D</sub>	DC (T <sub>c</sub> =60°C)	300	A	
	I <sub>DRM</sub>	Pulse (T <sub>c</sub> =60°C) 1ms *2	600		
Source current *1	I <sub>S</sub>	DC (T <sub>c</sub> =60°C)	300		
	I <sub>SRM</sub>	Pulse (Tc=60°C) 1ms *2	600		
Total power disspation *3	Ptot	T <sub>c</sub> =25°C	1875	W	
Max Junction Temperature	T <sub>jmax</sub>		175		
Operating junction temperature	$T_jop$		-40 to150	°C	
Storage temperature	T <sub>stg</sub>		-40 to125		
Isolation voltage	Visol	Terminals to baseplate, f=60Hz AC 1min.	2500	Vrms	
Mounting torque	_	Main Terminals : M6 screw	4.5	N·m	
		Mounting to heat shink: M5 screw	3.5		

<sup>(\*1)</sup> Case temperature (T<sub>c</sub>) is defined on the surface of base plate just under the chips.

# Example of acceptable $V_{\text{GS}}$ waveform



<sup>(\*2)</sup> Repetition rate should be kept within the range where temperature rise if die should not exceed T<sub>j max</sub>.

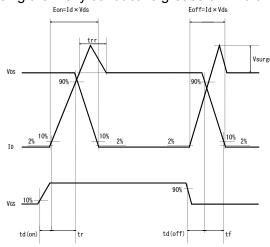
<sup>(\*3)</sup> T<sub>j</sub> is less than 175°C

## ●Electrical characteristics (T<sub>j</sub>=25°C)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
Static drain-source on-state voltage	V <sub>DS(on)</sub>	I <sub>D</sub> =300A, V <sub>GS</sub> =18V	T <sub>j</sub> =25°C	-	2.2	2.9	V
			T <sub>j</sub> =125°C	-	3.0	-	
			T <sub>j</sub> =150°C	-	3.4	4.5	
Drain cutoff current	I <sub>DSS</sub>	V <sub>DS</sub> =1200V, V <sub>GS</sub> =0V		-	-	3.2	mA
Source-drain voltage	$V_{SD}$	V <sub>GS</sub> =0V, I <sub>S</sub> =300A	T <sub>j</sub> =25°C	-	1.6	2.1	V
			T <sub>j</sub> =125°C		2.2	-	
			T <sub>j</sub> =150°C	-	2.4	3.2	
		V <sub>GS</sub> =18V, I <sub>S</sub> =300A	T <sub>j</sub> =25°C	-	1.4	-	
			T <sub>j</sub> =125°C		1.6	-	
			T <sub>j</sub> =150°C	-	1.7	-	
Gate-source threshold voltage	$V_{GS(th)}$	V <sub>DS</sub> =10V, I <sub>D</sub> =68mA		1.6	2.7	4.0	V
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =22V, V <sub>DS</sub> =0V		-	-	0.5	μΑ
		$V_{GS} = -6V, V_{DS} = 0V$		-0.5	-	-	
Switching characteristics	t <sub>d(on)</sub>	V <sub>GS(on)</sub> =18V, V <sub>GS(off)</sub> =0V		-	80	-	ns
	t <sub>r</sub>	$V_{DS}$ =600 $V$ $I_{D}$ =300 $A$ $R_{G}$ =0.2 $\Omega$ inductive load		-	70	-	
	t <sub>rr</sub>			ı	50	-	
	t <sub>d(off)</sub>			1	250	-	
	t <sub>f</sub>			-	65	-	
Input capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,100kHz		ı	35	-	nF
Gate Registance	$R_{Gint}$	T <sub>j</sub> =25°C		•	1.6	-	Ω
NTC Rated Resistance	R25				5.0		kΩ
NTC B Value	B50/25				3370		K
Stray Inductance	Ls				13	-	nΗ
Creepage Distance	-	Terminal to heat sink			14.5	-	mm
		Terminal to terminal			15.0	-	mm
Clearance Distance	-	Terminal to heat sink			12.0	-	mm
		Terminal to terminal			9.0	-	mm
Junction-to-case thermal resistance		DMOS (1/2 module) *4		-	-	80.0	K/W
		SBD (1/2 module) *4		•	-	0.11	
Case-to-heat sink	R <sub>th</sub> (c-f)	Case to heat sink, per 1 module,			0.035	-	
Thermal resistance	i V <sub>th</sub> (O <sup>3</sup> I)	Thermal grease appied *5			0.000		

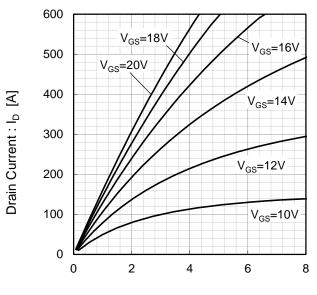
<sup>(\*4)</sup> Measurement of  $T_c$  is to be done at the point just beneath the chip.

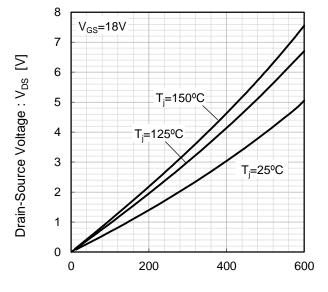
## Waveform for switching test



<sup>(\*5)</sup> Typical value is measured by using thermally conductive grease of  $\lambda$ =0.9W/(m·K).

Fig.1 Typical Output Characteristics [T<sub>i</sub>=25°C] Fig.2 Drain-Source Voltage vs. Drain Current





Drain-Source Voltage :  $V_{DS}$  [V]

Drain Current : I<sub>D</sub> [A]

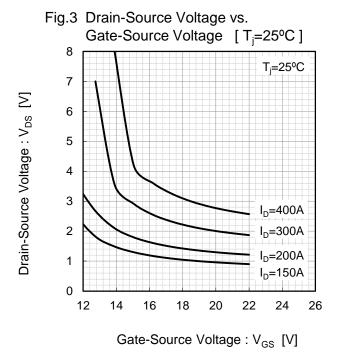
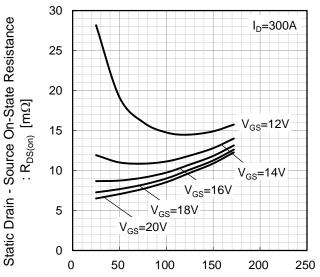
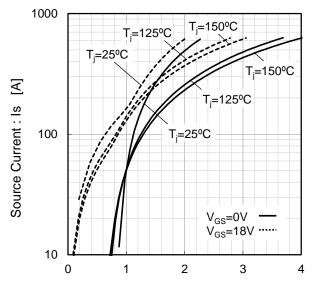


Fig.4 Static Drain - Source On-State Resistance vs. Junction Temperature



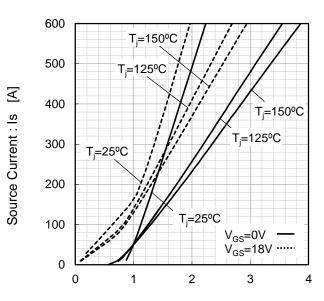
Junction Temperature : T<sub>i</sub> [°C]

Fig.5 Forward characteristic of Diode



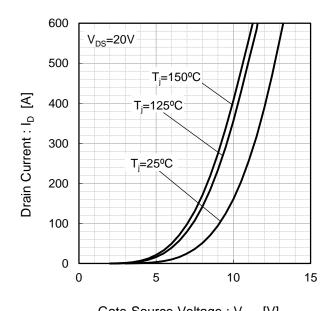
Source-Drain Voltage: V<sub>SD</sub> [V]

Fig.6 Forward characteristic of Diode



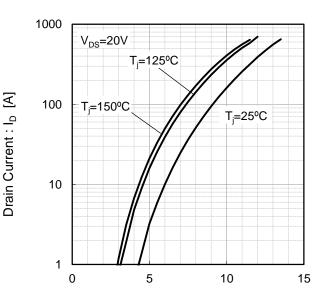
Source-Drain Voltage: V<sub>SD</sub> [V]

Fig.7 Drain Current vs. Gate-Source Voltage



Gate-Source Voltage :  $V_{GS}$  [V]

Fig.8 Drain Current vs. Gate-Source Voltage



Gate-Source Voltage : V<sub>GS</sub> [V]

Fig.9 Switching Characteristics [T<sub>i</sub>=25°C]

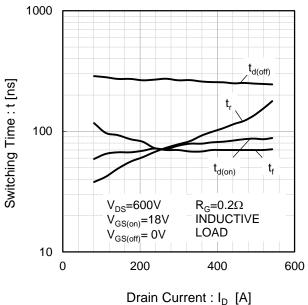
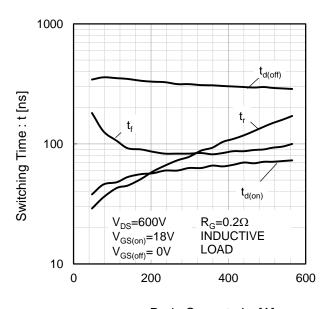
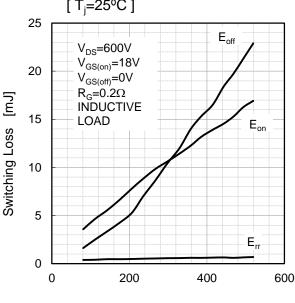


Fig.10 Switching Characteristics [T<sub>i</sub>=150°C]



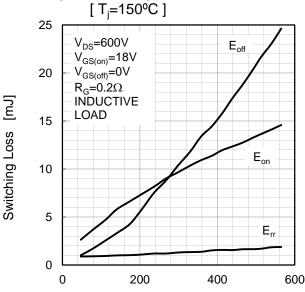
ent : I<sub>D</sub> [A] Drain Current : I<sub>D</sub> [A]

Fig.11 Switching Loss vs. Drain Current [ T<sub>i</sub>=25°C ]

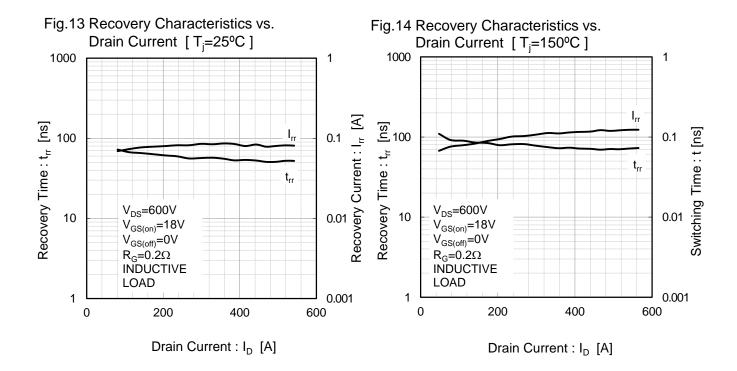


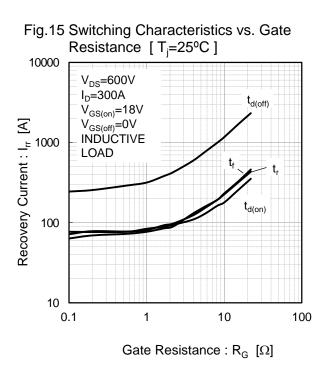
Drain Current : I<sub>D</sub> [A]

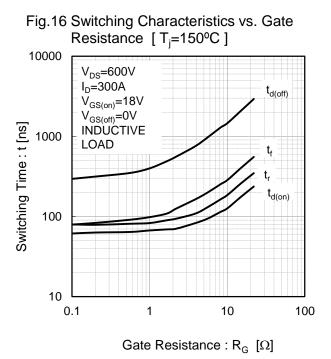
Fig.12 Switching Loss vs. Drain Current



Drain Current : I<sub>D</sub> [A]







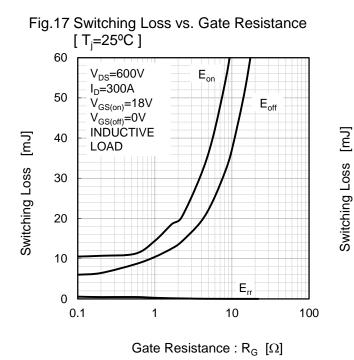
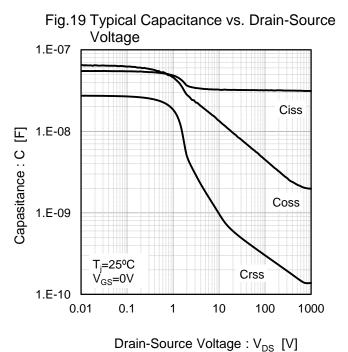
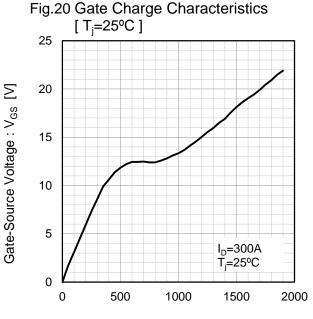


Fig.18 Switching Loss vs. Gate Resistance  $[T_i=150^{\circ}C]$ 60  $V_{DS} = 600V$  $I_{D} = 300A$ 50  $V_{GS(on)}=18V$   $V_{GS(off)}=0V$ INDUCTIVE 40 LOAD 30  $\mathsf{E}_{\mathsf{off}}$ 20  $\mathsf{E}_{\mathsf{on}}$ 10  $E_{rr}$ 0 10 100 0.1

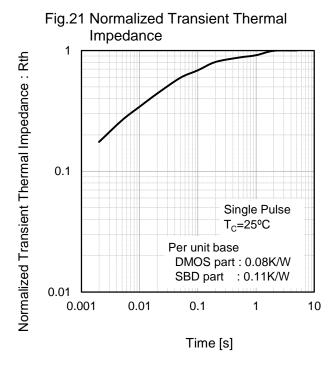
Gate Resistance :  $R_G$  [ $\Omega$ ]







Total Gate charge : Qg [nC]



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